

MMBTA05LT1, MMBTA06LT1

MMBTA06LT1 is a Preferred Device

Driver Transistors

NPN Silicon

Features

- Pb-Free Packages are Available

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage MMBTA05LT1 MMBTA06LT1	V_{CEO}	60 80	Vdc
Collector–Base Voltage MMBTA05LT1 MMBTA06LT1	V_{CBO}	60 80	Vdc
Emitter–Base Voltage	V_{EBO}	4.0	Vdc
Collector Current – Continuous	I_C	500	mAdc

THERMAL CHARACTERISTICS

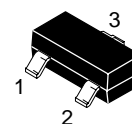
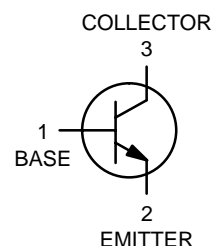
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{stg}	–55 to +150	$^\circ\text{C}$

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

- FR–5 = $1.0 \times 0.75 \times 0.062$ in.
- Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.

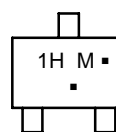


ON Semiconductor®

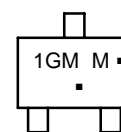


SOT-23
CASE 318
STYLE 6

MARKING DIAGRAMS



MMBTA05LT1



MMBTA06LT1

1H, 1GM = Specific Device Code
M = Date Code
▪ = Pb-Free Package
(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

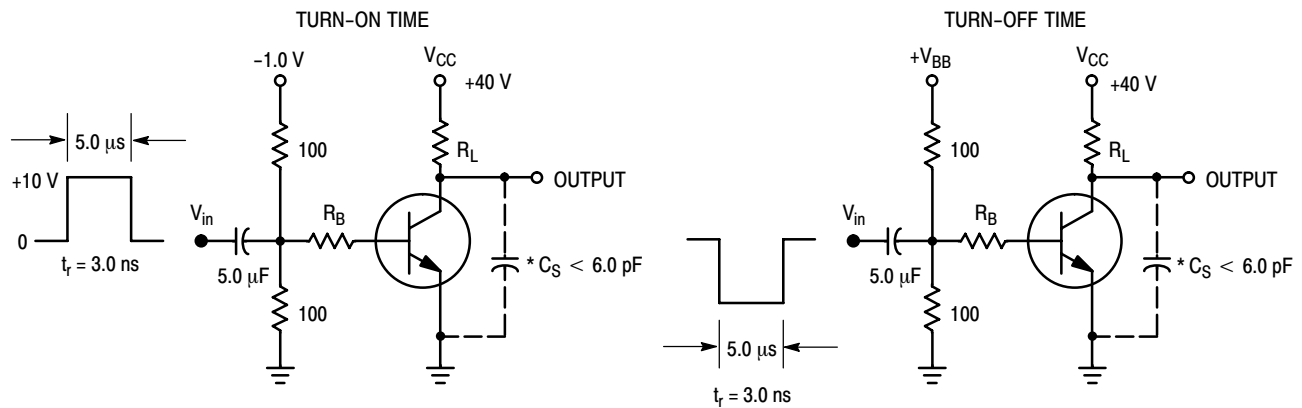
Preferred devices are recommended choices for future use and best overall value.

MMBTA05LT1, MMBTA06LT1

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Breakdown Voltage (Note 3) ($I_C = 1.0\text{ mAdc}$, $I_B = 0$)	$V_{(BR)CEO}$	60 80	–	Vdc
Emitter–Base Breakdown Voltage ($I_E = 100\ \mu\text{Adc}$, $I_C = 0$)	$V_{(BR)EBO}$	4.0	–	Vdc
Collector Cutoff Current ($V_{CE} = 60\text{ Vdc}$, $I_B = 0$)	I_{CES}	–	0.1	μAdc
Collector Cutoff Current ($V_{CB} = 60\text{ Vdc}$, $I_E = 0$) ($V_{CB} = 80\text{ Vdc}$, $I_E = 0$)	I_{CBO}	– –	0.1 0.1	μAdc
ON CHARACTERISTICS				
DC Current Gain ($I_C = 10\text{ mAdc}$, $V_{CE} = 1.0\text{ Vdc}$) ($I_C = 100\text{ mAdc}$, $V_{CE} = 1.0\text{ Vdc}$)	h_{FE}	100 100	– –	–
Collector–Emitter Saturation Voltage ($I_C = 100\text{ mAdc}$, $I_B = 10\text{ mAdc}$)	$V_{CE(sat)}$	–	0.25	Vdc
Base–Emitter On Voltage ($I_C = 100\text{ mAdc}$, $V_{CE} = 1.0\text{ Vdc}$)	$V_{BE(on)}$	–	1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current–Gain – Bandwidth Product (Note 4) ($I_C = 10\text{ mA}$, $V_{CE} = 2.0\text{ V}$, $f = 100\text{ MHz}$)	f_T	100	–	MHz

- Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2.0\%$.
- f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.



*Total Shunt Capacitance of Test Jig and Connectors
For PNP Test Circuits, Reverse All Voltage Polarities

Figure 1. Switching Time Test Circuits

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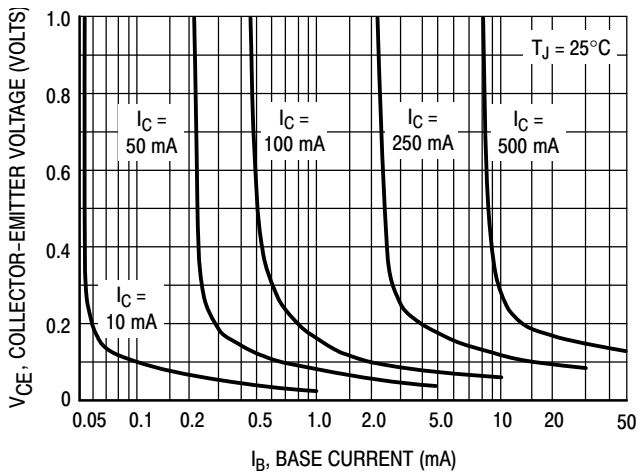


Figure 7. Collector Saturation Region

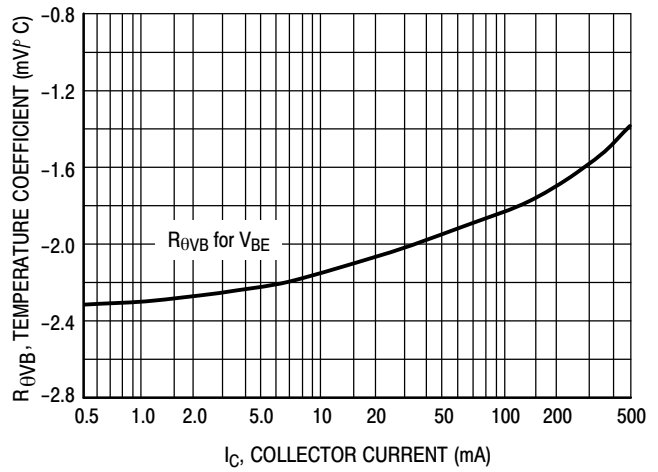


Figure 8. Base-Emitter Temperature Coefficient

ORDERING INFORMATION

Device	Package	Shipping†
MMBTA05LT1	SOT-23	3000 / Tape & Reel
MMBTA05LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
MMBTA05LT3	SOT-23	10,000 / Tape & Reel
MMBTA05LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
MMBTA06LT1	SOT-23	3000 / Tape & Reel
MMBTA06LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
MMBTA06LT3	SOT-23	10,000 / Tape & Reel
MMBTA06LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

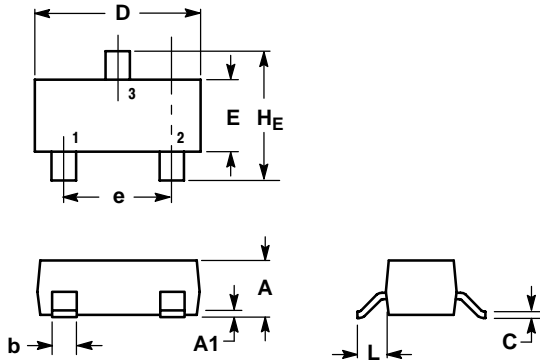
MMBTA05LT1, MMBTA06LT1

PACKAGE DIMENSIONS

SOT-23 (TO-236)

CASE 318-08

ISSUE AL



NOTES:

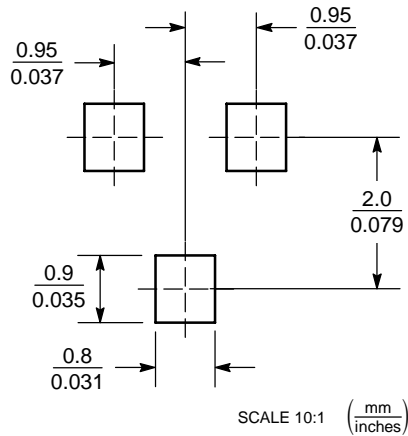
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318-01 THRU -07 AND -09 OBSOLETE, NEW STANDARD 318-08.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.081
L	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104

STYLE 6:

- PIN 1. BASE
2. EMITTER
3. COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.